L Number	Hits	Search Text	DB	Time stamp
-	833		USPAT;	2003/03/10 10:42
			EPO; JPO;	1
			DERWENT	!
-	672	438/633	USPAT;	2001/12/17 14:40
			EPO; JPO;	, }
	45004		DERWENT	2001/12/10 14 06
-	45384	barrier adj (layer or film)	USPAT;	2001/12/18 14:06
	i		EPO; JPO;	
	1055	(barrier adj (layer or film)) and (reduc\$4	DERWENT USPAT;	2001/12/18 08:16
_	1055	adj (gas or agent or chemical))	EPO; JPO;	1 2001/12/10 00:10
		adj (gas of agent of chemical)	DERWENT	, ,
_	237	((barrier adj (layer or film)) and	USPAT;	2001/12/18 08:17
		(reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	
		and (metal adj (film or layer))	DERWENT	į
-	5	(barrier adj (layer or film)) and (first	USPAT;	2001/12/17 14:56
		adj reduc\$4 adj (gas or agent or	EPO; JPO;	i
		chemical))	DERWENT	
-	0	1 ((USPAT;	2001/12/17 14:53
		adj reduc\$4 adj (gas or agent or	EPO; JPO;	
		chemical))) and (metal adj (film or	DERWENT	·
	_	layer))	IICDAM.	2001/12/17 14:55
-	0	(((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical)))	USPAT; EPO; JPO;	2001/12/1/ 14:55
		and (metal adj (film or layer))) and	DERWENT	
		(second adj reduc\$4 adj (gas or agent or	DUMBNI	
		chemical))		
_	237	1	USPAT;	2001/12/17 14:55
		(reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	
		and (metal adj (film or layer))) and	DERWENT	
		(reduc\$4 adj (gas or agent or chemical))		1 1
_	163	, , , , , , , , , , , , , , , , , , , ,	USPAT;	; 2001/12/17 14:58 _i
		chemical))	EPO; JPO;	i I
			DERWENT	
-	92		USPAT;	2001/12/17 15:01
		chemical))) and (second adj reduc\$4 adj	EPO; JPO;	
	6	(gas or agent or chemical)) (((first adj reduc\$4 adj (gas or agent or	DERWENT	2001/12/17 15:01
-	0	chemical))) and (second adj reduc\$4 adj	USPAT; EPO; JPO;	2001/12/17 13:01
		(gas or agent or chemical))) and	DERWENT	
		semiconductor	DEKWENT	
_	683		USPAT;	2001/12/17 15:31
		100,02	EPO; JPO;	
			DERWENT	
-	1178	438/643	USPAT;	2002/01/02 14:19
			EPO; JPO;	!
			DERWENT	1
-	20851		USPAT;	2001/12/18 14:01
		adj (layer or film))	EPO; JPO;	
	20.	11114: 55 200 24: 12	DERWENT	1 2001 /12 /10 00 13
-	394	((((diffus\$6 adj barrier) or prevent\$10)	USPAT;	2001/12/18 08:17
		adj (layer or film))) and (reduc\$4 adj	EPO; JPO;	1
_	96	<pre>(gas or agent or chemical)) ((((diffus\$6 adj barrier) or prevent\$10)</pre>	DERWENT USPAT;	2001/12/18 12:54
ļ	20	adj (layer or film))) and (reduc\$4 adj	EPO; JPO;	2001/12/10 12.34
		(gas or agent or chemical))) and (metal	DERWENT	
		adj (film or layer))		!
_	20851		USPAT;	2001/12/18 14:02
:		adj (layer or film))	EPO; JPO;	
			DERWENT	
- 1	3447	(((diffus\$6 adj barrier) or (diffus\$6 adj	USPAT;	2001/12/18 14:04
1		prevent\$10)) adj (layer or film))	EPO; JPO;	
			DERWENT	
-	40	((((diffus\$6 adj barrier) or prevent\$10)	USPAT;	2001/12/18 14:07
		adj (layer or film))) and (first adj	EPO; JPO;	
		anneal\$5)	DERWENT	2001/10/10 1: 05
-	0		USPAT;	2001/12/18 14:08
		adj (layer or film))) and (first adj	EPO; JPO;	•
		anneal\$5)) and (second adj aneal\$5)	DERWENT	l

-	45418	barrier adj (layer or film)	USPAT; EPO; JPO;	2003/03/07	13:53
-	147	(barrier adj (layer or film)) and (first adj anneal\$5)	DERWENT USPAT; EPO; JPO;	2001/12/18	14:08
-	0	((barrier adj (layer or film)) and (first adj anneal\$5)) and (second adj aneal\$5)	DERWENT USPAT; EPO; JPO;	2001/12/18	14:21
_	483098	plug or interconnection	DERWENT USPAT; EPO; JPO;	2001/12/18	14:23
-	108014	metal adj (layer or film)	DERWENT USPAT; EPO; JPO;	2001/12/18	14:24
-	18975	(metal adj (layer or film)) and (plug or interconnect\$5)	DERWENT USPAT; EPO; JPO;	2001/12/18	14:25
-	3544	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5	DERWENT USPAT; EPO; JPO;	2001/12/18	14:25
-	56	interconnect\$5)) and anneal\$5) and	DERWENT USPAT; EPO; JPO; DERWENT	2001/12/18	14:30
_	6	adj anneal\$5)) and (reduc\$3 adj	USPAT; EPO; JPO;	2001/12/18	14:31
	40	or interconnect\$5)) and anneal\$5) and (reduc\$3 adj atmosphere)) and	DERWENT USPAT; EPO; JPO; DERWENT	2001/12/18	14:37
-	6	(first adj anneal\$5)) and (reduc\$3 adj	USPAT; EPO; JPO;	2001/12/18	14:36
_	5	atmosphere)) and semiconductor (("5116463") or ("6207222") or ("6197688") or ("6191031") or ("6143646")).PN.	DERWENT USPAT	2002/01/02	14:18
-	562		USPAT; EPO; JPO; DERWENT	2002/01/02	14:19
_	55733	barrier adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/10	07:56
-	489	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07	14:01
-	160	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07	14:03
-	3	(((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07	14:08
_	222	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient)) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07	14:05
-	3	((((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07	13:59
L	<u> </u>		IBM TDB	L	

113				 -	77000 400 400	
adj (layer or film)) and plasma (barrier adj (layer or film)) and (reducs) or (hydrogen or ("H. sub.2")) adj (gas or ambient)) (barrier adj (layer or film)) and (reducs) or (hydrogen or ("H. sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) (continue) and (metal adj (layer or film)) and (reducs) or (hydrogen or ("H. sub.2")) adj (gas or ambient)) and (reducs) adj (gas or ambient)) and (metal adj (layer or film)) and (reducs) are (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reducs) are (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (second	-	113	, , ,	USPAT;	2003/03/07	14:06
DEMENT: IBM TOB				1		1
28226			adj (layer of lilm)// and plasma			
28226 (barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) (foarrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) (foarrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) (foarrier adj (layer or film)) (foarrier adj (layer or				1		
Or (hygrogen or ("H.sub.2")) adj (gas or ambient)	_	28226	(barrier adj (layer or film)) and (reduc\$3		2003/03/07	14:03
### ### #### #########################				US-PGPUB;		
184 184 184 185			1	EPO; JPO;		
G490 ((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) Common or film) Common or film) Common or mablent) Com				DERWENT;	!	•
(reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (reduc\$3 adj (gas or ambient)) and (reduc\$3 adj (gas or ambient)) and (reduc\$3 adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (payer or film)) and (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (payer or film)) and (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (second adj (gas or mabient)) and (reduc\$3 or (hygrogen or ("H. sub.2")) adj (gas or ambient)) and (second adj (gas or mabient)) and second adj (gas or mabient)) and (second adj (gas or mabient))						
Guas or ambient)) and (metal adj (layer or film))	-	6490			' 2003/03/07	14:05
Or film	!	1		:	:	
222		İ		1		
Clearrier adj (layer or film) and (reduc\$3 adj (gas or ambient)) and (reduc\$3 adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor ambient)) and semiconductor ambient)) and (reduc\$3 adj (gas or ambient))) and semiconductor (reduc\$3 adj (gas or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and ((hyprogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and semiconductor) and metal adj (layer or film)) and semiconductor) and metal adj (layer or film)) and semiconductor) and metal adj (layer or f			or film))			
(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and plasma	_	222	//harrior adi /laver or film)) and	-	2003/03/07	14.07
Gas or ambienti) and (reduc\$3 adj (gas or ambient) and plasma (teduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient) and plasma ((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and plasma (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (second adj (gas or ambient)) and (second adj (gas or ambient) and (second adj (gas or ambient) and (second adj (gas or ambient) and (second adj (aser) or (hydrogen or ("H. sub.2")))) and semiconductor ("H. sub.2")))) and semiconductor) and (second adj (aser) and (second adj (aser) and (second adj (aser) and (se	_	222	,		2003/03/07	14.07
Sample						
Sample S						
Sample		•	or ambrency, and prasma	1	,	
	_	8105	((barrier adj (layer or film)) and		2003/03/07	14:07
Gas or ambient))) and plasma				US-PGPUB;		
3403			(gas or ambient))) and plasma	EPO; JPO;		
3403				DERWENT;		
(gas or ambient)) and (metal adj (layer or film)) and plasma	-	3403	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		2003/03/07	14:07
Or film)) and plasma						
18M TDB						
99			or film))) and plasma			
Creduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient))			///bannian adi /lanan an film\\ and		2002/02/07	14.07
(gas or ambient)) and (metal adj (layer or film)) and (second adj (gas or ambient)) - 99 ((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (second adj (gas or ambient))) and (second adj (aper or film)) and (second adj (layer or film)) and (second adj (lay	_	99			2003/03/07	14:07
or film)) and (second adj (gas or ambient)) ((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) - 92 ((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (second adj (gas or or film)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient))) and semiconductor - 25099 barrier adj (layer or film) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor - 3856 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (metal			(reduces of (hygrogen of (h.sub.2)) adj			į
ambient)		1		1		ļ
99			1	1		i
(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film))) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and (second adj (gas or ambient))) and semiconductor	_	99	1		2003/03/07	14:10
(gas or ambient)) and (metal adj (layer or film)) and (second adj (gas or ambient)) and (second adj (gas or ambient)) (((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor - 25099 barrier adj (layer or film) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) - 3856 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor - 1694 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film) and (lay						
ambient)) and (second adj (gas or ambient)) (((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and second adj (gas or ambient))) and semiconductor 25099 barrier adj (layer or film) and (barrier adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))) (reduc\$3 or (hydrogen or ("H.sub.2")))) (reduc\$3 or (reduc\$3 or (hydrogen or ("H.sub.2")))) and semiconductor 1694 (reduc\$3 or anneal\$5) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj vapor adj deposition)) (reduc\$3 or anneal\$5) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor)				EPO; JPO;		
ambient)) (((((barrier adj (layer or film)) and (reduc\$3 or (hydrogen or ("H.sub.2")) adj (gas or ambient))) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor - 25099 barrier adj (layer or film) - 3856 (barrier adj (layer or film)) and (reduc\$3 adj (gas or anneal\$5) and ((reduc\$3 adj (gas or (logarier adj (layer or film))) and semiconductor - 3856 ((barrier adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2")))) and semiconductor - 1694 ((barrier adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj (gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (reduc\$3 adj (red			or film))) and (second adj (gas or	DERWENT;		
92				IBM_TDB	İ	
(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient)) and (metal adj (layer or film))) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor IBM_TDB IBM_TDB						
(gas or ambient))) and (metal adj (layer or film)) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor barrier adj (layer or film) - 25099 (barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) - 3856 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor - 1694 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) - 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))	-	92	(((((barrier adj (layer or film)) and		2003/03/07	14:10
or film)) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor 25099 barrier adj (layer or film) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2")))) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2")))) and semiconductor (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2")))) and semiconductor (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2")))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2"))))) and semiconductor) and ((metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2"))))) and semiconductor) and ((metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H. sub.2"))))) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film)) and semiconductor) and (layer or film) and (layer or film)) and semiconductor)						
ambient))) and (second adj (gas or ambient))) and semiconductor USPAT 2003/03/10 07:56 25099 barrier adj (layer or film) Ospat USPAT 2003/03/10 08:01 USPAT 2003/03/10 08:02 USPAT 2003/03/10 08:03 USPAT 2003/03/10 08:04 USPAT 2003/03/10 08:05 USPAT 2003/03						
ambient))) and semiconductor barrier adj (layer or film) ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) same (chemical adj vapor adj deposition)) 60 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (expos\$3 or anneal\$5) and (reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and semiconductor)				1		İ
25099 barrier adj (layer or film) 7320 (barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor 1694 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) 303 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and ((metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and ((metal adj (layer or film)) and ((cxpos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and semiconductor)				1014_100		
- 7320 (barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) - 3856 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor - 1694 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) - 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or semiconductor) and semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and (metal adj (layer or semiconductor) and semiconductor) and semiconductor) and semiconductor) and semiconductor) and semiconductor semiconductor semiconductor semiconductor semiconductor semi	_	25099		USPAT	2003/03/10	07:56
((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor 1694 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))	_			l .		1
gases) or (hydrogen or ("H.sub.2")))) ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor)						
- 3856 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor - 1694 ((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) and						
gases) or (hydrogen or ("H.sub.2")))) and semiconductor (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film))	_	3856	((barrier adj (layer or film)) and	USPAT	2003/03/10	08:02
semiconductor (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) 60 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) and semiconductor) and (metal adj (layer or film))			((expos\$3 or anneal\$5) and ((reduc\$3 adj		Ī	İ
- 1694 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) - 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or			1 -		1	j
((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or		1			1	
gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film)) 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or	-	1694		USPAT	2003/03/10	08:03
semiconductor) and (metal adj (layer or film)) - 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						
film)) (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or					l	
- 303 (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						İ
((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or	_	202		מעם אות	2003/02/10	ا ممنوم
gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or	-	303		USPAT	2003/03/10	00:04
semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition)) - 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						
film)) same (chemical adj vapor adj deposition)) - 60 ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or]
deposition)) - 60 ((((barrier adj (layer or film)) and (USPAT 2003/03/10 08:05 ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						
- 60 ((((barrier adj (layer or film)) and (SPAT 2003/03/10 08:05 ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						!
((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or	_	60		USPAT	2003/03/10	08:05
gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or						
semiconductor) and (metal adj (layer or		1				
		<u> </u>				

-	9	((((barrier adj (layer or film)) and	USPAT	2003/03/10 08:05
		((expos\$3 or anneal\$5) and ((reduc\$3 adj		
		gases) or (hydrogen or ("H.sub.2")))) and	į	1
		semiconductor) and ((metal adj (layer or		1
•		film)) same (chemical adj vapor adj		1
		deposition))) and (second adj gas)		
	2	(("5665659") or ("5953634")).PN.	USPAT	2003/03/10 10:42